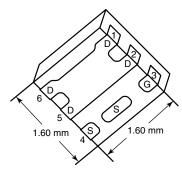




## P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY								
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)					
	0.058 at V <sub>GS</sub> = - 4.5 V	- 9 <sup>a</sup>						
- 20	0.077 at V <sub>GS</sub> = - 2.5 V	- 9 <sup>a</sup>	7.6 nC					
	0.105 at V <sub>GS</sub> = - 1.8 V	- 5						

### PowerPAK SC-75-6L-Single



### **Ordering Information:**

SiB433EDK-T1-GE3 (Lead (Pb)-free and Halogen-free)

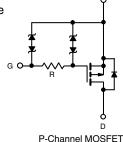
### **FEATURES**

- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-75 Package
  - Small Footprint Area
  - Low On-Resistance
- 100 %  $\rm R_{\rm g}$  Tested Typical ESD Performance 2000 V
- Built in ESD Protection with Zener Diode
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

### **APPLICATIONS**

Load Switch for Portable Devices

Charger Switch for Portable **Devices** 



HALOGEN FREE

Ma	arking Co	ode
Part # code —	BLX •XXX	Lot Traceability and Date code

Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	$V_{DS}$	- 20	V				
Gate-Source Voltage	V <sub>GS</sub>	± 8	v				
	T <sub>C</sub> = 25 °C		- 9 <sup>a</sup>				
Continuous Drain Current (T <sub>.1</sub> = 150 °C)	T <sub>C</sub> = 70 °C	_	- 9 <sup>a</sup>				
Continuous Diain Current (1) = 130 C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 5.3 <sup>b, c</sup>				
	T <sub>A</sub> = 70 °C		- 4.3 <sup>b, c</sup>	A			
Pulsed Drain Current		I <sub>DM</sub>	- 20				
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I-	- 9 <sup>a</sup>				
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	- 2 <sup>b, c</sup>				
	T <sub>C</sub> = 25 °C		13				
Maximum Power Dissipation	T <sub>C</sub> = 70 °C	ь	8.4	□ w			
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.4 <sup>b, c</sup>	VV			
	T <sub>A</sub> = 70 °C		1.6 <sup>b, c</sup>	$\neg$			
Operating Junction and Storage Temperature Ra	ange	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C			
Soldering Recommendations (Peak Temperature	e) <sup>d, e</sup>		260				

THERMAL RESISTANCE RATINGS								
Parameter	Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	41	51	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	7.5	9.5	G/ <b>V V</b>			

### Notes:

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 105 °C/W.

Document Number: 65652 S12-0979-Rev. B, 30-Apr-12 For technical support, please contact: pmostechsupport@vishav.com



<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C)  Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	- Cymison	1991 Conditions		.,,,,	muxi		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$			- 13			
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = - 250 μA		2.5		mV/°C	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.4		- 1	V	
·		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 6		
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5		
		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 15			Α	
	(* )	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 3.7 A		0.047	0.058		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 3.2 A		0.064	0.077	Ω	
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 1.5 A		0.085	0.105		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 3.7 A		12		S	
Dynamic <sup>b</sup>		25					
•		V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 8 V, I <sub>D</sub> = - 5.3 A		14	21	nC	
Total Gate Charge	$Q_g$	20 / GO / D		7.6	12		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -5.3 \text{ A}$		0.8			
Gate-Drain Charge	Q <sub>gd</sub>			3.1			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.4	2	4	kΩ	
Turn-On Delay Time	t <sub>d(on)</sub>			0.2	0.3		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_{L} = 2.3 \Omega$		1	1.5	- - - μs	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 4.3 A, $V_{GEN}$ = - 4.5 V, $R_g$ = 1 $\Omega$		4	6		
Fall Time	t <sub>f</sub>			2	3		
Turn-On Delay Time	t <sub>d(on)</sub>			0.09	0.14		
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, R_{L} = 2.3 \Omega$		0.4	0.6		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 4.3 A, $V_{GEN}$ = - 8 V, $R_g$ = 1 $\Omega$		5.2	7.8		
Fall Time	t <sub>f</sub>	2(3.1)		2.3	3.5	1	
<b>Drain-Source Body Diode Characterist</b>	ics			•	l		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 9	Α	
Pulse Diode Forward Current	I <sub>SM</sub>				- 20	_ ^	
Body Diode Voltage	$V_{SD}$	I <sub>S</sub> = - 4.3 A, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			30	60	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = - 4.3 A, dl/dt = 100 A/μs, T <sub>.I</sub> = 25 °C		20	40	nC	
Reverse Recovery Fall Time	t <sub>a</sub>	1		13		20	
Reverse Recovery Rise Time	t <sub>b</sub>			17		ns	

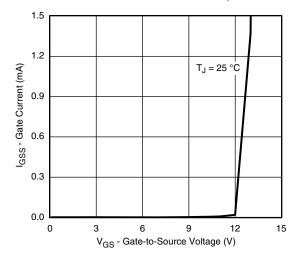
### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

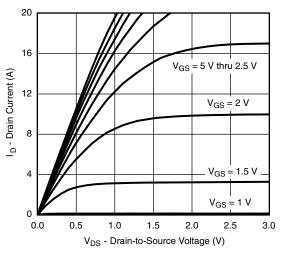
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



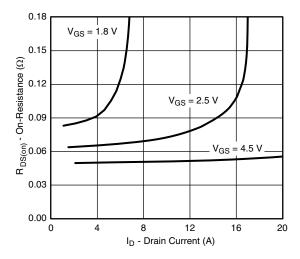
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



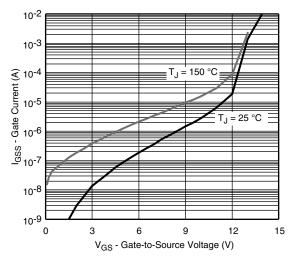
### Gate Current vs. Gate-Source Voltage



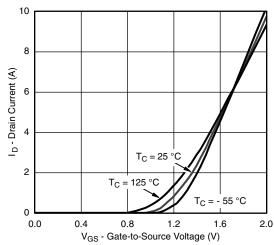
### **Output Characteristics**



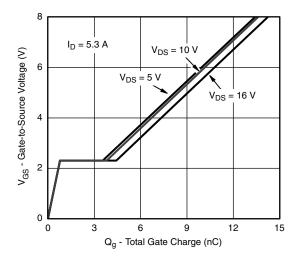
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage

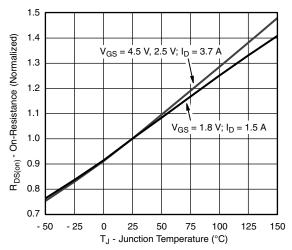


Transfer Characteristics

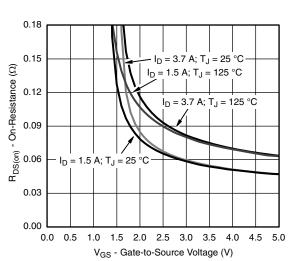


**Gate Charge** 

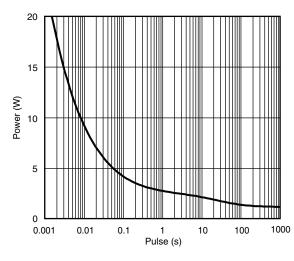
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



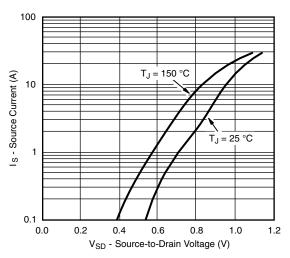
On-Resistance vs. Junction Temperature



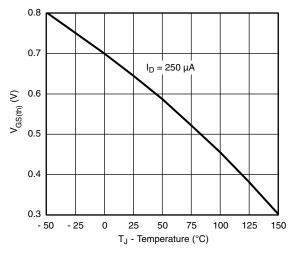
On-Resistance vs. Gate-to-Source Voltage



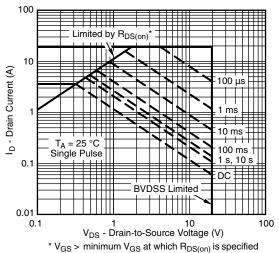
Single Pulse Power, Junction-to-Ambient



Soure-Drain Diode Forward Voltage



Threshold Voltage



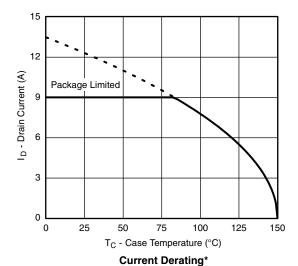
Safe Operating Area, Junction-to-Ambient

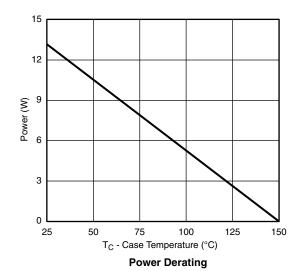






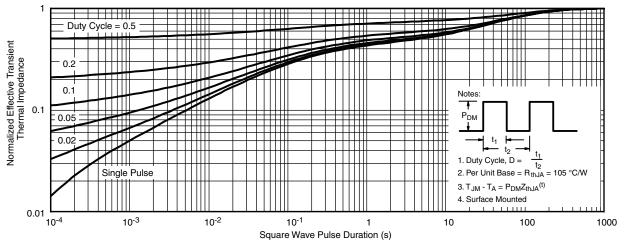
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



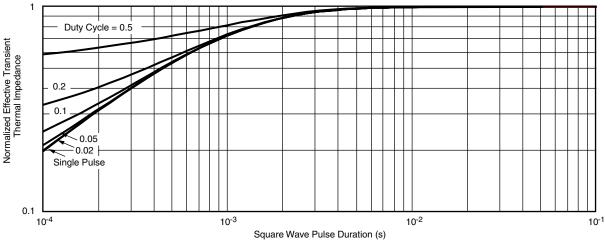


 $<sup>^*</sup>$  The power dissipation  $P_D$  is based on  $T_{J(max)}$  = 150  $^{\circ}$ C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package

### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

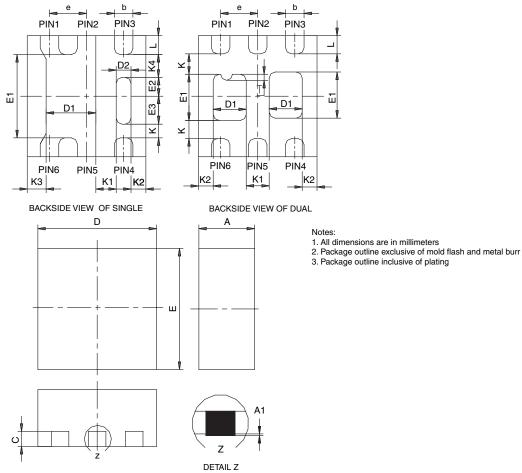


Normalized Thermal Transient Impedance, Junction-to-Case

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## PowerPAK® SC75-6L



A A1 b C	Min 0.675 0 0.18 0.15 1.53 0.57	Nom 0.75 - 0.25 0.20 1.60	Max 0.80 0.05 0.33 0.25	Min 0.027 0 0.007 0.006	Nom 0.030 - 0.010	Max 0.032 0.002	Min 0.675	Nom 0.75	Max 0.80	<b>Min</b> 0.027	Nom 0.030	<b>Max</b> 0.032
A1 b	0.675 0 0.18 0.15 1.53	0.75 - 0.25 0.20	0.80 0.05 0.33 0.25	0.027 0 0.007	0.030	0.032 0.002	0.675	0.75				
A1 b	0 0.18 0.15 1.53	- 0.25 0.20	0.05 0.33 0.25	0 0.007	-	0.002			0.80	0.027	0.030	0.032
b C	0.18 0.15 1.53	0.25 0.20	0.33 0.25	0.007			0					
С	0.15 1.53	0.20	0.25		0.010		•	-	0.05	0	-	0.002
_	1.53			0.006		0.013	0.18	0.25	0.33	0.007	0.010	0.013
D		1.60	1 70	0.500	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
	0.57		1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
D1		0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021
D2	0.10	0.20	0.30	0.004	0.008	0.012						
E	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028
E2	0.20	0.25	0.30	0.008	0.010	0.012						
E3	0.32	0.37	0.42	0.013	0.015	0.017						
е		0.50 BSC			0.020 BSC			0.50 BSC			0.020 BSC	
K		0.180 TYP			0.007 TYP			0.245 TYP			0.010 TYP	
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP		
K2		0.200 TYP			0.008 TYP		0.200 BSC		0.008 TYP			
КЗ		0.255 TYP			0.010 TYP	l						
K4		0.300 TYP			0.012 TYP	P						
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014
Т							0.03	0.08	0.13	0.001	0.003	0.005

ECN: C-07431 - Rev. C, 06-Aug-07

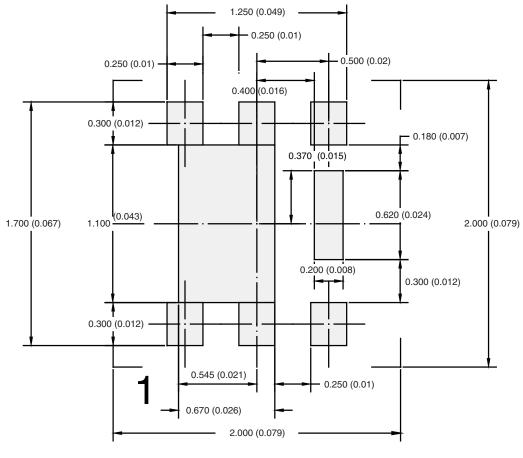
DWG: 5935

Document Number: 73000 06-Aug-07

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## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NO



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